



Docket No.: 57810-077

PATENT

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re Application of

Yasuhiko NOMURA, et al:

Serial No.: 10/663,707

Filed: September 17, 2003

For: NITRIDE-BASED SEMICONDUCTOR LASER DEVICE

: Customer Number: 20277
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: Confirmation Number: 3966
:
: Group Art Unit: 2828
:
: Examiner:
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INFORMATION DISCLOSURE STATEMENT

Mail Stop IDS
Commissioner for Patents
P.O. Box 1450
Alexandria, VA 22313-1450

Dear Sir:

In accordance with the provisions of 37 C.F.R. 1.56, 1.97 and 1.98, the attention of the Patent and Trademark Office is hereby directed to the documents listed on the attached form PTO-1449. It is respectfully requested that the documents be expressly considered during the prosecution of this application, and that the documents be made of record therein and appear among the "References Cited" on any patent to issue therefrom.

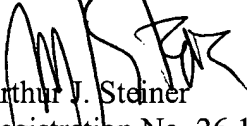
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10/663,707

Please charge any shortage in fees due in connection with the filing of this paper, including extension of time fees, to Deposit Account 500417 and please credit any excess fees to such deposit account.

Respectfully submitted,

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INFORMATION DISCLOSURE CITATION IN AN APPLICATION

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57810-077

SERIAL NO.
10/663,707

APPLICANT
Yasuhiko NOMURA, et al.

FILING DATE
September 17, 2003

GROUP
2828

(PTO-1449)

U.S. PATENT DOCUMENTS

| EXAMINER'S INITIALS | CITE NO. | Document Number Number-Kind Codez (if known) | Publication Date MM-DD-YYYY | Name of Patentee or Applicant of Cited Document | Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear |
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FOREIGN PATENT DOCUMENTS

| EXAMINER'S INITIALS | CITE NO. | Foreign Patent Document Country Codes -Number 4 -Kind Codes (if known) | Publication Date MM-DD-YYYY | Name of Patentee or Applicant of Cited Document | Pages, Columns, Lines Where Relevant Figures Appear | Translation | |
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OTHER ART (Including Author, Title, Date, Pertinent Pages, Etc.)

| EXAMINER'S INITIALS | CITE NO. | Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published. |
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| | | H. Amano, et al. "Metalorganic vapor phase epitaxial growth of a high quality GaN film using an AlN buffer layer." Appl. Phys. Lett., Vol. 48, No. 5, 3 February 1986. pp. 353-355 |

EXAMINER

DATE CONSIDERED

*EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

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